



Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.



ON Semiconductor®

December 2016

FGAF40N60SMD

600 V, 40 A Field Stop IGBT

Features

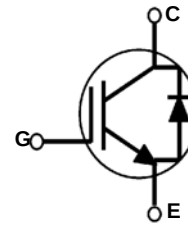
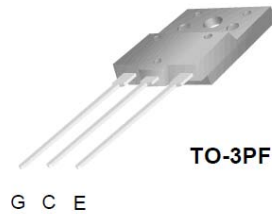
- Maximum Junction Temperature : $T_J = 175^{\circ}\text{C}$
- Positive Temperature Co-efficient for easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.9 \text{ V(Typ.) @ } I_C = 40 \text{ A}$
- High Input Impedance
- Fast Switching: $E_{OFF} = 6.5 \text{ uJ/A}$
- Tightened Parameter Distribution
- RoHS Compliant

Applications

- Sewing Machine, CNC
- Home Appliances, Motor-Control

General Description

Using novel field stop IGBT technology, ON semiconductor's new series of field stop 2nd generation IGBTs offer the optimum performance for solar inverter, UPS, welder and PFC applications where low conduction and switching losses are essential.



Absolute Maximum Ratings

Symbol	Description	Ratings	Unit
V_{CES}	Collector to Emitter Voltage	600	V
V_{GES}	Gate to Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C = 25^{\circ}\text{C}$	80*	A
	Collector Current @ $T_C = 100^{\circ}\text{C}$	40*	A
$I_{CM(1)}$	Pulsed Collector Current	120*	A
I_F	Diode Forward Current @ $T_C = 25^{\circ}\text{C}$	40*	A
	Diode Forward Current @ $T_C = 100^{\circ}\text{C}$	20*	A
$I_{FM(1)}$	Pulsed Diode Maximum Forward Current	120*	A
P_D	Maximum Power Dissipation @ $T_C = 25^{\circ}\text{C}$	115	W
	Maximum Power Dissipation @ $T_C = 100^{\circ}\text{C}$	58	W
T_J	Operating Junction Temperature	-55 to +175	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55 to +175	$^{\circ}\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^{\circ}\text{C}$

Notes:

*Drain current limited by maximum junction temperature

1: Repetitive rating: Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case	-	1.3	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}(\text{Diode})$	Thermal Resistance, Junction to Case	-	3.27	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	$^{\circ}\text{C}/\text{W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGAF40N60SMD	FGAF40N60SMD	TO-3PF	-	-	30

Electrical Characteristics of the IGBT $T_C = 25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV _{CES}	Collector to Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 250μA	600	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0V, I _C = 250μA	-	0.6	-	V/°C
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0V	-	-	250	μA
I _{GES}	G-E Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	-	-	±400	nA
On Characteristics						
V _{GE(th)}	G-E Threshold Voltage	I _C = 250μA, V _{CE} = V _{GE}	3.5	4.5	6.0	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 40A, V _{GE} = 15V	-	1.9	-	V
		I _C = 40A, V _{GE} = 15V, T _C = 175°C	-	2.1	-	V
Dynamic Characteristics						
C _{ies}	Input Capacitance	V _{CE} = 30V, V _{GE} = 0V, f = 1MHz	-	1880	-	pF
C _{oes}	Output Capacitance		-	180	-	pF
C _{res}	Reverse Transfer Capacitance		-	50	-	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{CC} = 400V, I _C = 40A, R _G = 6Ω, V _{GE} = 15V, Inductive Load, T _C = 25°C	-	12	-	ns
t _r	Rise Time		-	20	-	ns
t _{d(off)}	Turn-Off Delay Time		-	92	-	ns
t _f	Fall Time		-	13	17	ns
E _{on}	Turn-On Switching Loss		-	0.87	-	mJ
E _{off}	Turn-Off Switching Loss		-	0.26	0.34	mJ
E _{ts}	Total Switching Loss		-	1.13	-	mJ
t _{d(on)}	Turn-On Delay Time	V _{CC} = 400V, I _C = 40A, R _G = 6Ω, V _{GE} = 15V, Inductive Load, T _C = 175°C	-	15	-	ns
t _r	Rise Time		-	22	-	ns
t _{d(off)}	Turn-Off Delay Time		-	116	-	ns
t _f	Fall Time		-	16	-	ns
E _{on}	Turn-On Switching Loss		-	0.97	-	mJ
E _{off}	Turn-Off Switching Loss		-	0.60	-	mJ
E _{ts}	Total Switching Loss		-	1.57	-	mJ

Electrical Characteristics of the IGBT (Continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Unit
Q_g	Total Gate Charge	$V_{CE} = 400V, I_C = 40A,$ $V_{GE} = 15V$	-	119	-	nC
Q_{ge}	Gate to Emitter Charge		-	13	-	nC
Q_{gc}	Gate to Collector Charge		-	58	-	nC

Electrical Characteristics of the Diode $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max	Unit
V _{FM}	Diode Forward Voltage	I _F = 20A	T _C = 25 ^o C	-	2.3	-	V
			T _C = 175 ^o C	-	1.67	-	
E _{rec}	Reverse Recovery Energy	I _F =20A, dI _F /dt = 200A/μs	T _C = 175 ^o C	-	48.9	-	uJ
t _{rr}	Diode Reverse Recovery Time		T _C = 25 ^o C	-	36	-	ns
			T _C = 175 ^o C	-	110	-	
Q _{rr}	Diode Reverse Recovery Charge		T _C = 25 ^o C	-	46.8	-	nC
			T _C = 175 ^o C	-	445	-	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

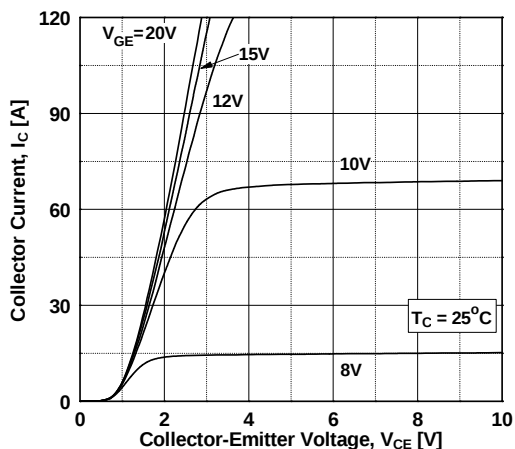


Figure 2. Typical Output Characteristics

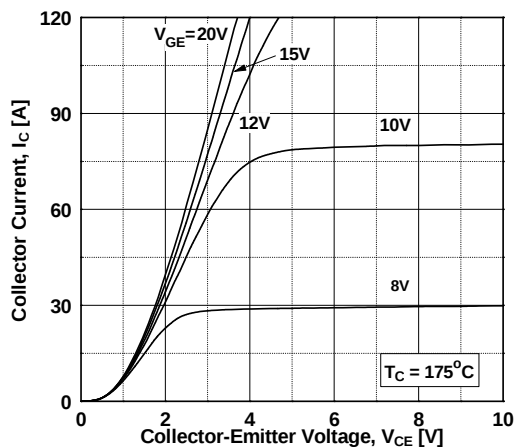


Figure 3. Typical Saturation Voltage Characteristics

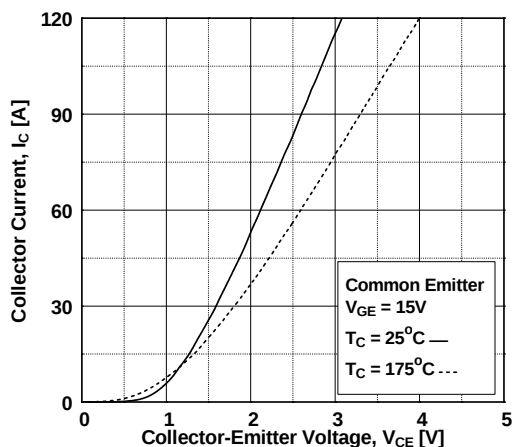


Figure 4. Transfer Characteristics

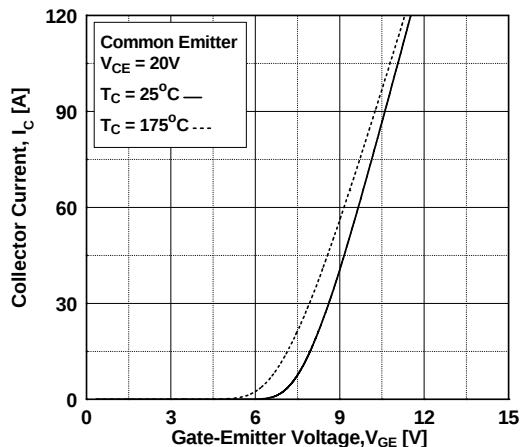


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

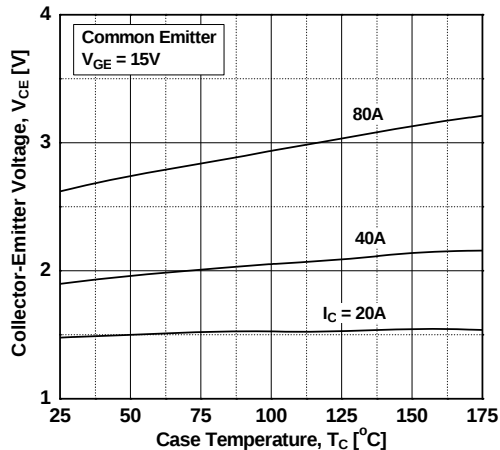
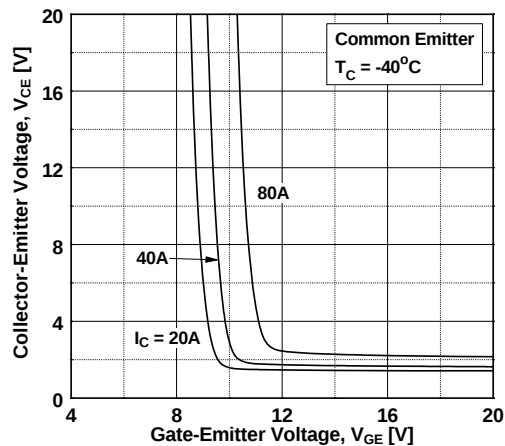


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. V_{GE}

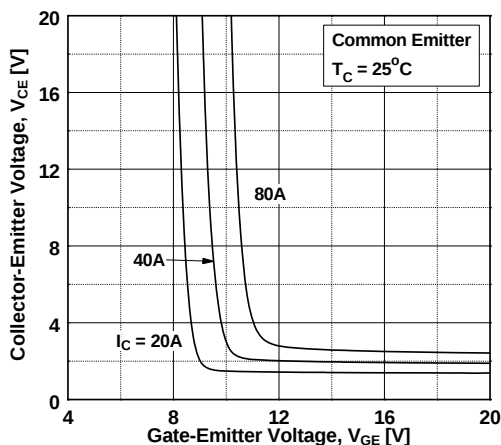


Figure 8. Saturation Voltage vs. V_{GE}

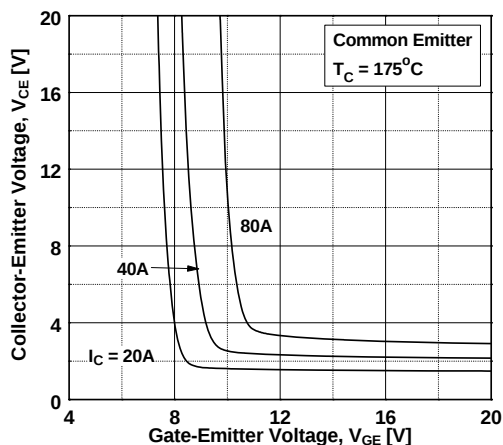


Figure 9. Capacitance Characteristics

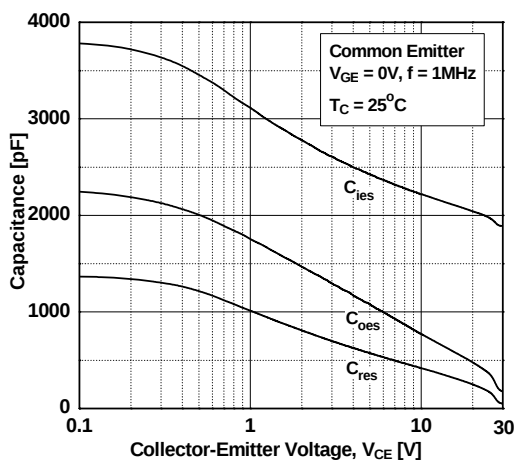


Figure 10. Gate charge Characteristics

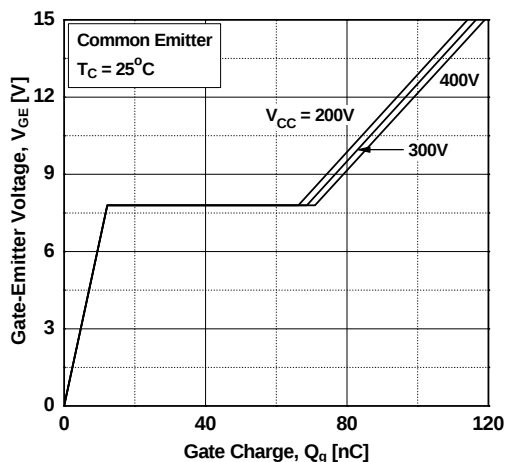


Figure 11. SOA Characteristics

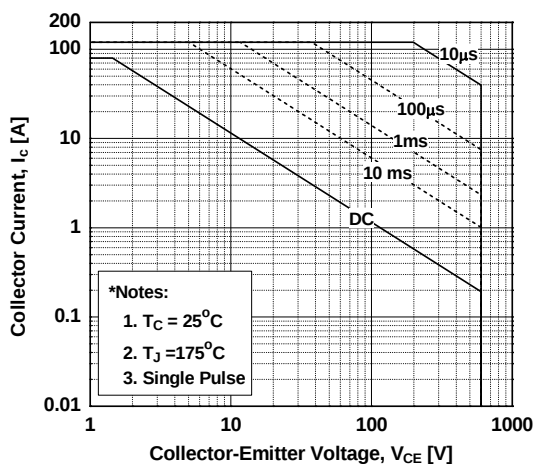
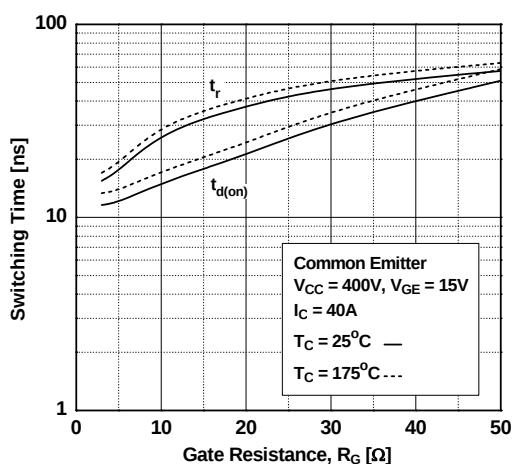


Figure 12. Turn-on Characteristics vs. Gate Resistance



Typical Performance Characteristics

Figure 13. Turn-off Characteristics vs. Gate Resistance

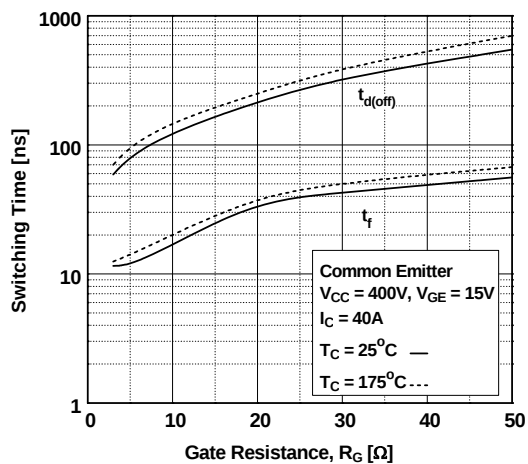


Figure 14. Turn-on Characteristics vs. Collector Current

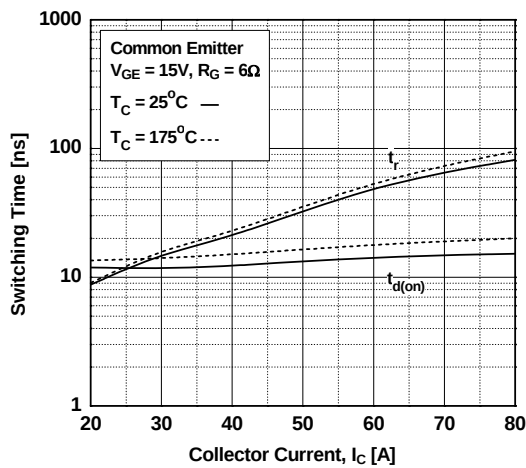


Figure 15. Turn-off Characteristics vs. Collector Current

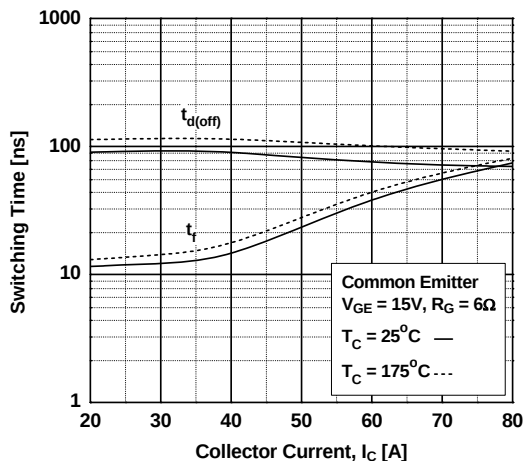


Figure 16. Switching Loss vs. Gate Resistance

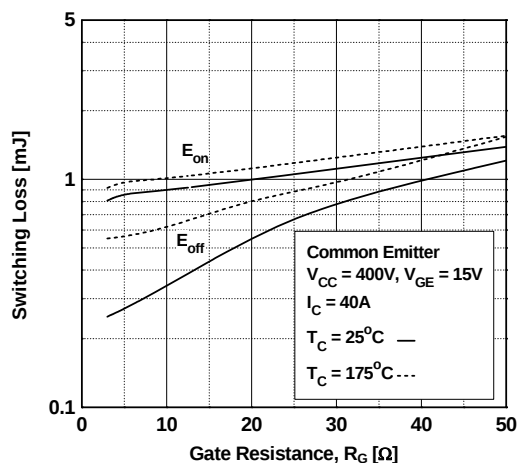


Figure 17. Switching Loss vs. Collector Current

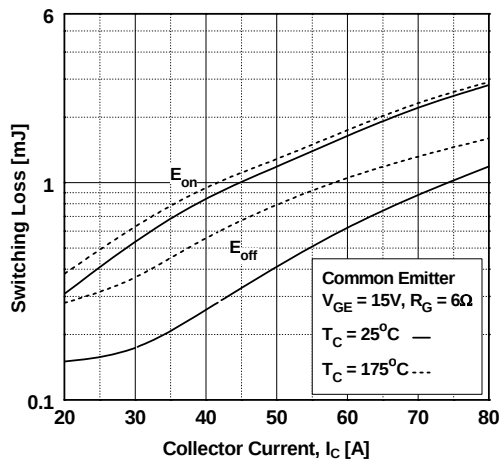
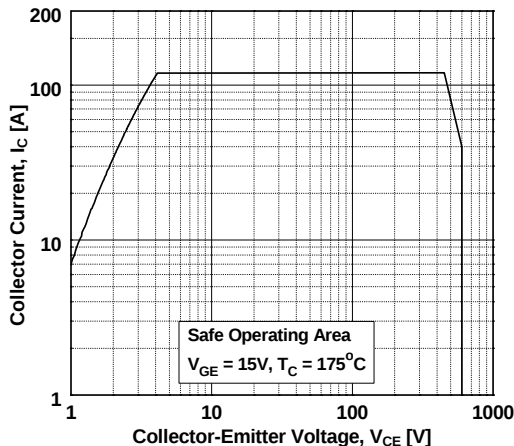


Figure 18. Turn off Switching SOA Characteristics



Typical Performance Characteristics

Figure 19. Current Derating

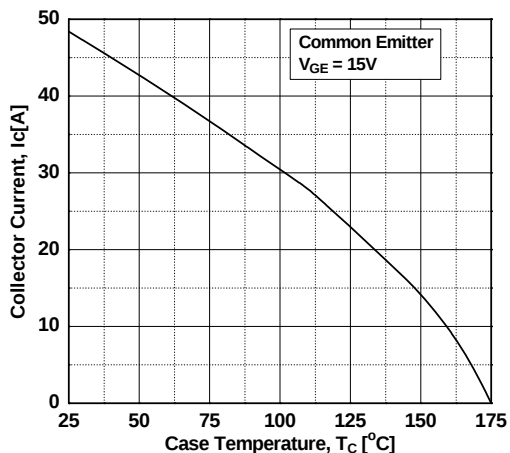


Figure 20. Power Dissipation

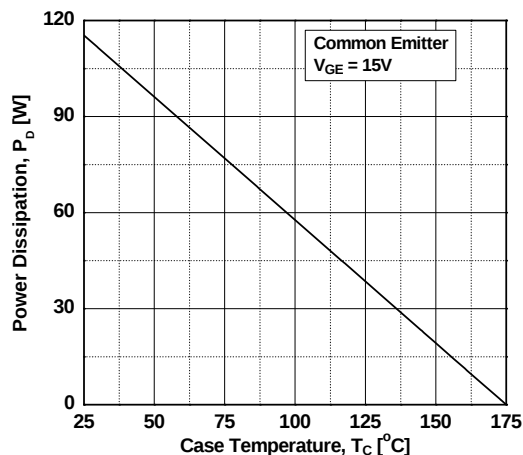


Figure 21. Load Current Vs. Frequency

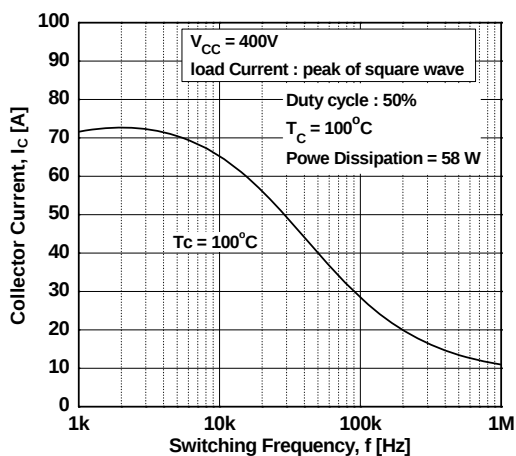


Figure 22. Forward Characteristics

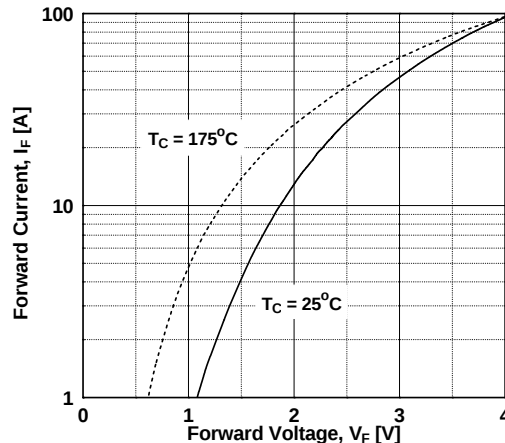


Figure 23. Reverse Current

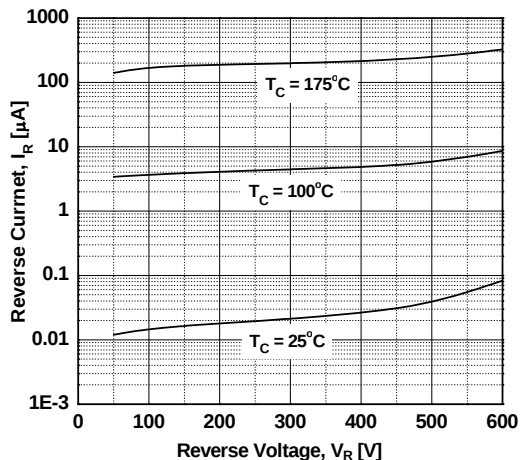
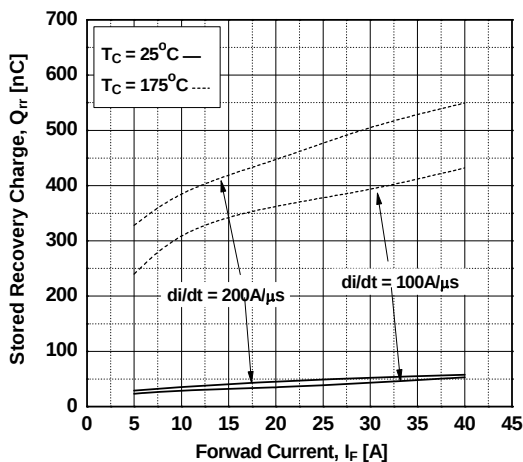


Figure 24. Stored Charge



Typical Performance Characteristics

Figure 25. Reverse Recovery Time

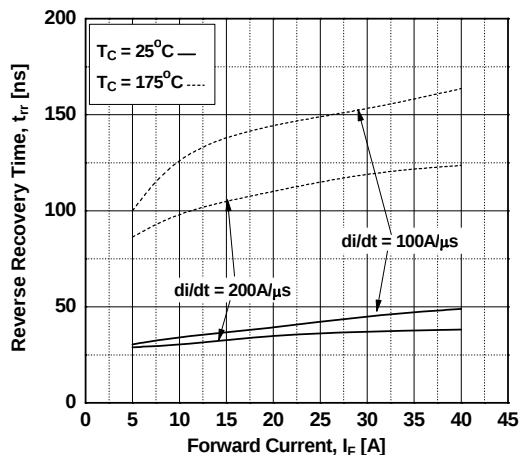


Figure 26. Transient Thermal Impedance of IGBT

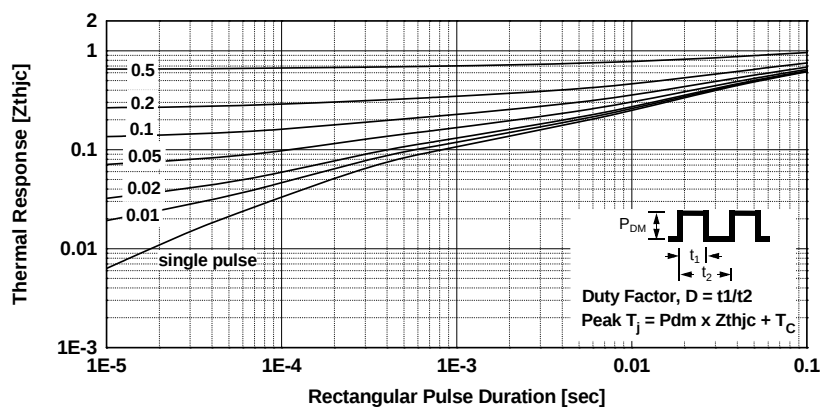
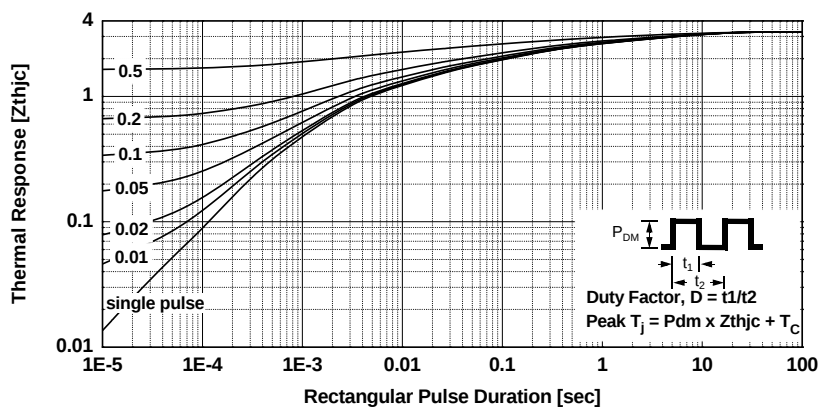
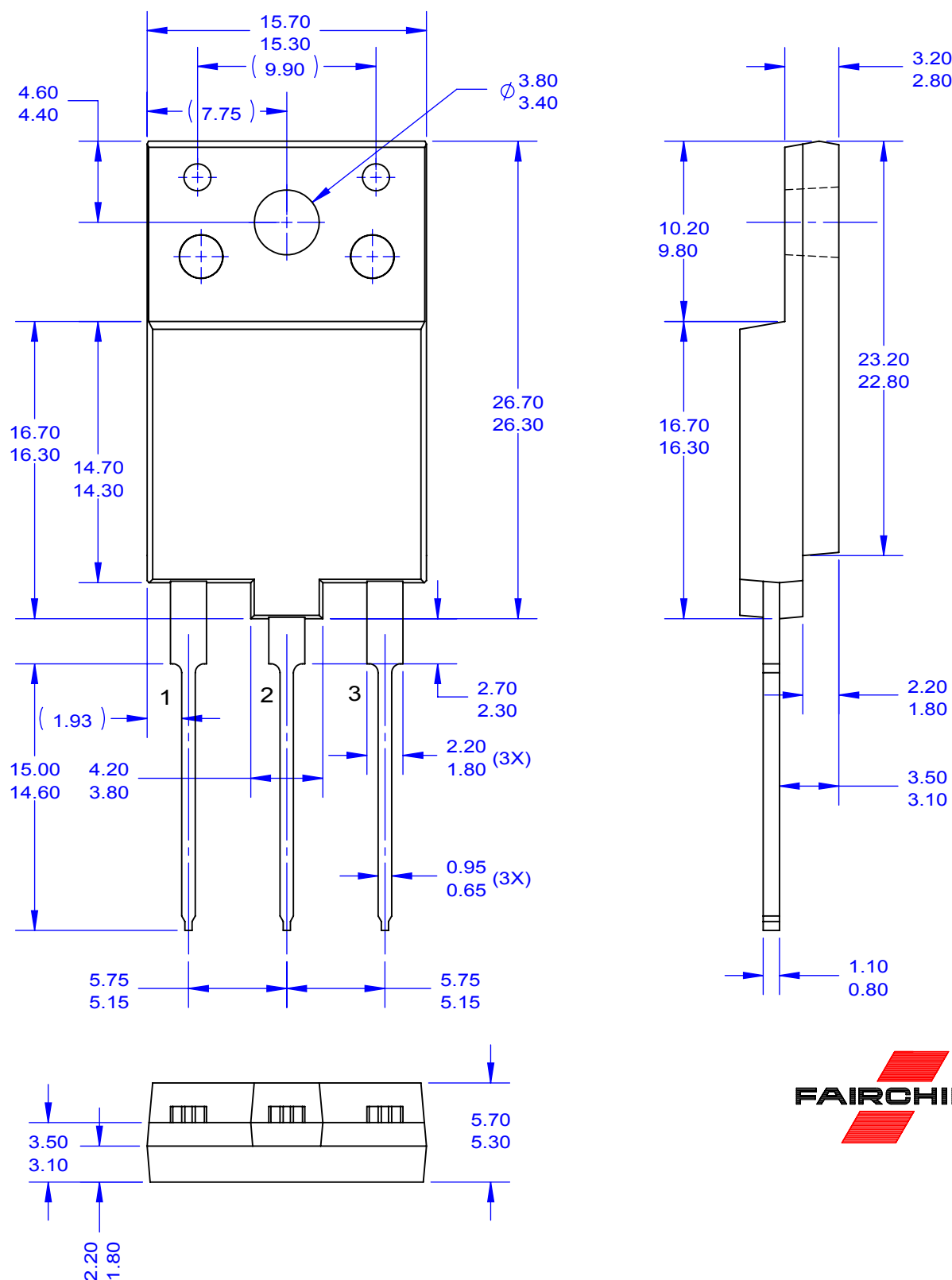


Figure 27. Transient Thermal Impedance of Diode





NOTES:

- THIS PACKAGE CONFORMS TO SC94 JEITA PACKAGING STANDARD.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- PIN 2 CONNECTS TO DAP.
- DRAWING FILE NAME: TO3PFA03REV2

ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada

Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910

Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local
Sales Representative